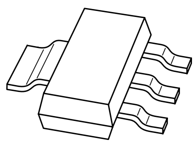


# PBHV8215Z

**150 V, 2 A NPN high-voltage low $V_{CEsat}$ (BISS) transistor**

**Rev. 01 — 11 November 2009** **Product data sheet**

## 1. Product profile

### 1.1 General description

NPN high-voltage low $V_{CEsat}$ Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9215Z.

### 1.2 Features

- High voltage
- Low collector-emitter saturation voltage $V_{CEsat}$
- High collector current capability $I_C$ and $I_{CM}$
- High collector current gain ($h_{FE}$) at high $I_C$
- AEC-Q101 qualified
- Medium power SMD plastic package

### 1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

**Table 1. Quick reference data**

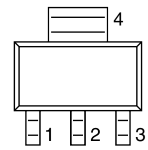
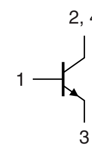
| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{CEO}$ | collector-emitter voltage | open base | | - | - | 150 | V |
| $I_C$ | collector current | | | - | - | 2 | A |
| $h_{FE}$ | DC current gain | $V_{CE}$ = 10 V; $I_C$ = 100 mA | [1] | 100 | 240 | - | |

[1] Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

founded by Philips

## 2. Pinning information

**Table 2. Pinning**

| Pin | Description | Simplified outline | Graphic symbol |
|---|---|---|---|
| 1 | base |  |  |
| 2 | collector | | |
| 3 | emitter | | |
| 4 | collector | | |

sym016

## 3. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PBHV8215Z | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 |

## 4. Marking

**Table 4. Marking codes**

| Type number | Marking code |
|---|---|
| PBHV8215Z | V8215Z |

# 5. Limiting values

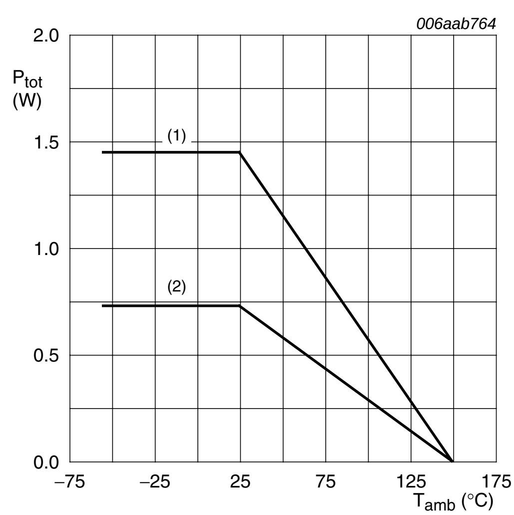
**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{CBO}$ | collector-base voltage | open emitter | | - | 350 | V |
| $V_{CEO}$ | collector-emitter voltage | open base | | - | 150 | V |
| $V_{EBO}$ | emitter-base voltage | open collector | | - | 6 | V |
| $I_C$ | collector current | | | - | 2 | A |
| $I_{CM}$ | peak collector current | single pulse; $t_p \leq 1$ ms | | - | 4 | A |
| $I_{BM}$ | peak base current | single pulse; $t_p \leq 1$ ms | | - | 500 | mA |
| $P_{tot}$ | total power dissipation | $T_{amb} \leq 25$ °C | [1] | - | 0.73 | W |
| | | | [2] | - | 1.45 | W |
| $T_j$ | junction temperature | | | - | 150 | °C |
| $T_{amb}$ | ambient temperature | | | –55 | +150 | °C |
| $T_{stg}$ | storage temperature | | | –65 | +150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 $cm^2$.




(1) FR4 PCB, mounting pad for collector 6 $cm^2$

(2) FR4 PCB, standard footprint

**Fig 1. Power derating curves**

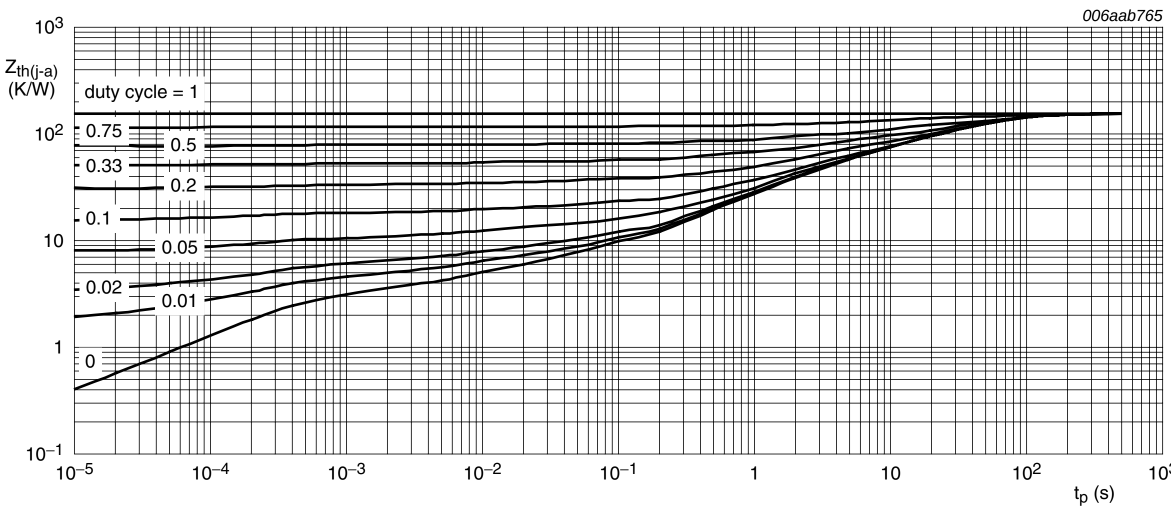
# 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 170 | K/W |
| | | | [2] | - | - | 85 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | - | 15 | K/W |

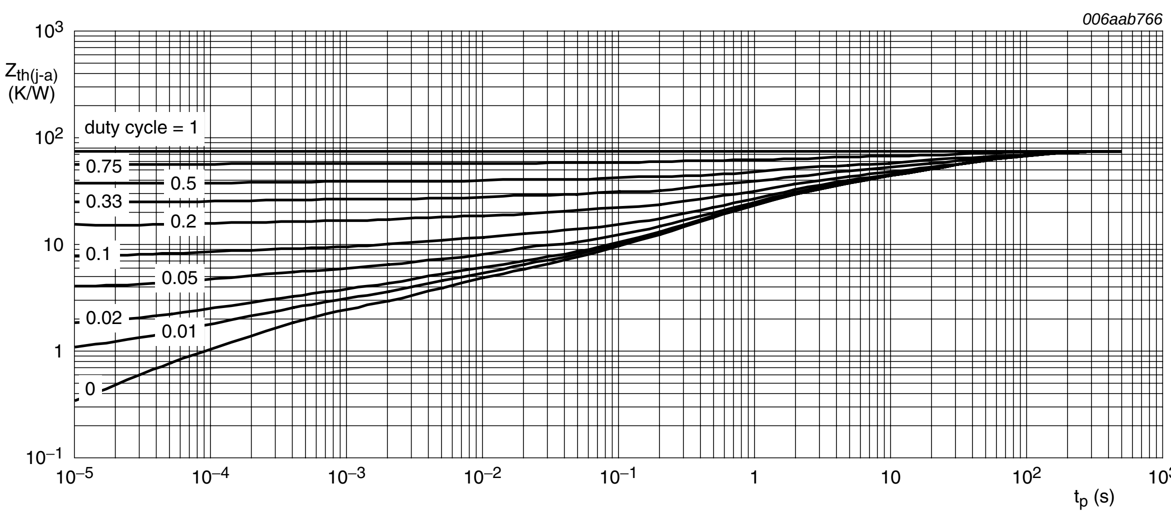
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 $cm^2$.




FR4 PCB, standard footprint

**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**




FR4 PCB, mounting pad for collector 6 $cm^2$

**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

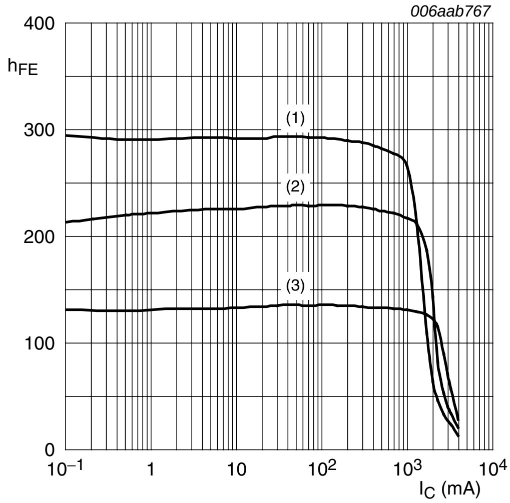
# 7. Characteristics

**Table 7. Characteristics**

*$T_{amb}$ = 25 °C unless otherwise specified.*

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $I_{CBO}$ | collector-base cut-off current | $V_{CB}$ = 120 V; $I_E$ = 0 A | | - | - | 100 | nA |
| | | $V_{CB}$ = 120 V; $I_E$ = 0 A; $T_j$ = 150 °C | | - | - | 10 | μA |
| $I_{CES}$ | collector-emitter cut-off current | $V_{CE}$ = 120 V; $V_{BE}$ = 0 V | | - | - | 100 | nA |
| $I_{EBO}$ | emitter-base cut-off current | $V_{EB}$ = 4 V; $I_C$ = 0 A | | - | - | 100 | nA |
| $h_{FE}$ | DC current gain | $V_{CE}$ = 10 V | | | | | |
| | | $I_C$ = 100 mA | [1] | 100 | 240 | - | |
| | | $I_C$ = 1 A | [1] | 100 | 230 | - | |
| | | $I_C$ = 1.5 A | [1] | 90 | 210 | - | |
| | | $I_C$ = 2 A | [1] | 55 | 130 | - | |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C$ = 100 mA; $I_B$ = 20 mA | [1] | - | 15 | 30 | mV |
| | | $I_C$ = 1 A; $I_B$ = 200 mA | [1] | - | 90 | 170 | mV |
| | | $I_C$ = 1.5 A; $I_B$ = 300 mA | [1] | - | 130 | 220 | mV |
| | | $I_C$ = 2 A; $I_B$ = 400 mA | [1] | - | 170 | 280 | mV |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C$ = 2 A; $I_B$ = 400 mA | [1] | - | 85 | 140 | mΩ |
| $V_{BEsat}$ | base-emitter saturation voltage | $I_C$ = 2 A; $I_B$ = 400 mA | [1] | - | 1.0 | 1.2 | V |
| $t_d$ | delay time | $V_{CC}$ = 6 V; $I_C$ = 0.5 A; $I_{Bon}$ = 0.1 A; $I_{Boff}$ = −0.1 A | | - | 20 | - | ns |
| $t_r$ | rise time | | | - | 280 | - | ns |
| $t_{on}$ | turn-on time | | | - | 300 | - | ns |
| $t_s$ | storage time | | | - | 2165 | - | ns |
| $t_f$ | fall time | | | - | 275 | - | ns |
| $t_{off}$ | turn-off time | | | - | 2440 | - | ns |
| $f_T$ | transition frequency | $V_{CE}$ = 10 V; $I_E$ = 10 mA; f = 100 MHz | | - | 33 | - | MHz |
| $C_c$ | collector capacitance | $V_{CB}$ = 20 V; $I_E$ = $i_e$ = 0 A; f = 1 MHz | | - | 17 | - | pF |
| $C_e$ | emitter capacitance | $V_{EB}$ = 0.5 V; $I_C$ = $i_c$ = 0 A; f = 1 MHz | | - | 500 | - | pF |

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



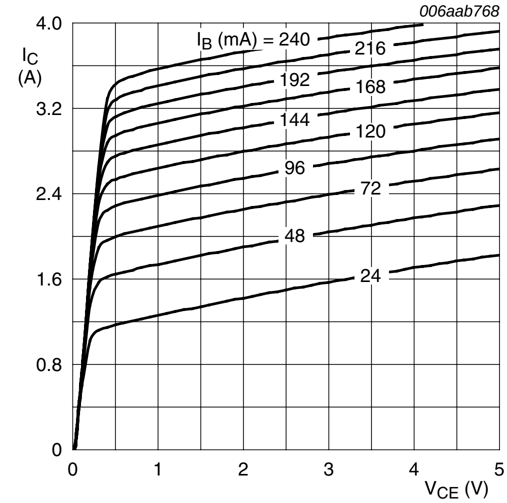

$V_{CE}$ = 10 V

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

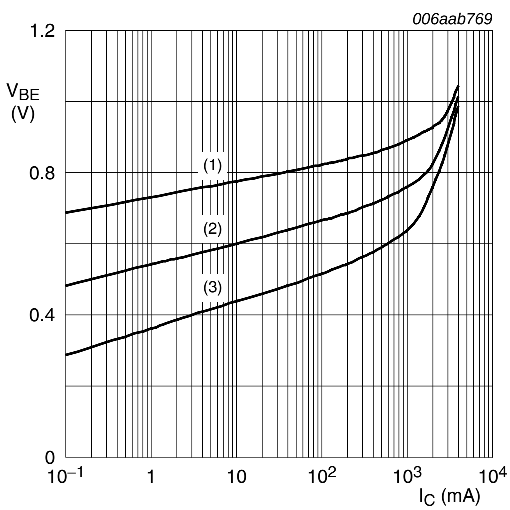
(3) $T_{amb}$ = −55 °C

**Fig 4. DC current gain as a function of collector current; typical values**




$T_{amb}$ = 25 °C

**Fig 5. Collector current as a function of collector-emitter voltage; typical values**



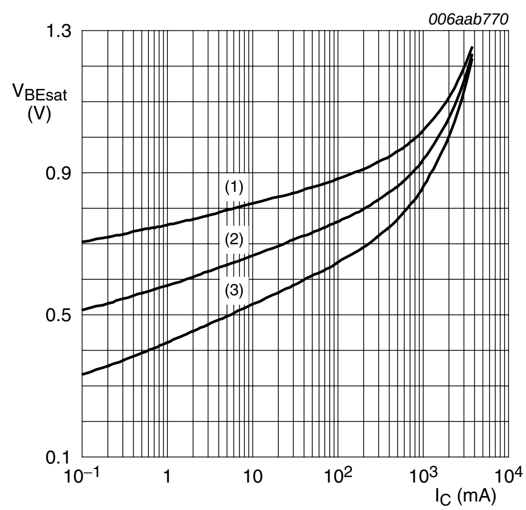

$V_{CE}$ = 10 V

(1) $T_{amb}$ = −55 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = 100 °C

**Fig 6. Base-emitter voltage as a function of collector current; typical values**



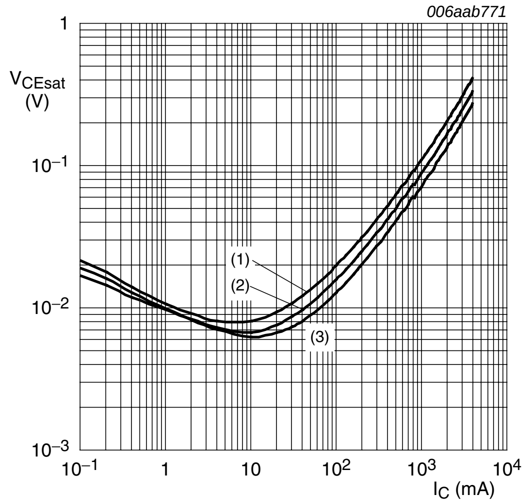

$I_C/I_B$ = 5

(1) $T_{amb}$ = −55 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = 100 °C

**Fig 7. Base-emitter saturation voltage as a function of collector current; typical values**



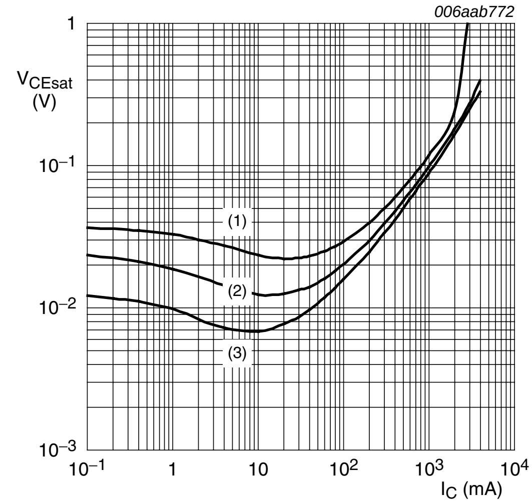

$I_C/I_B = 5$

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = −55 °C

**Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values**



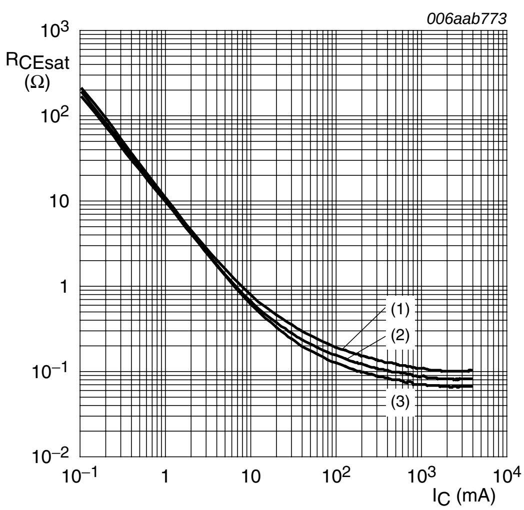

$T_{amb}$ = 25 °C

(1) $I_C/I_B = 20$

(2) $I_C/I_B = 10$

(3) $I_C/I_B = 5$

**Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values**



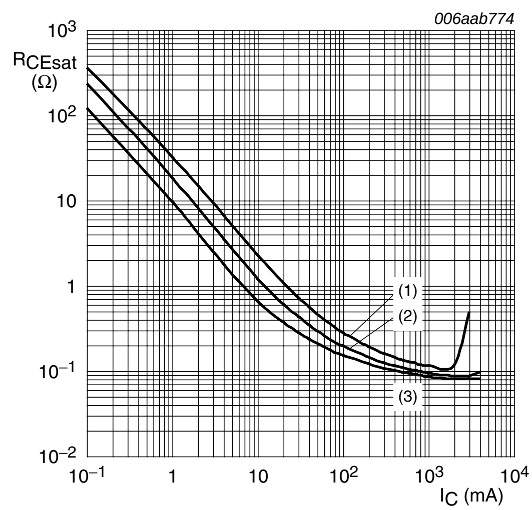

$I_C/I_B = 5$

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = −55 °C

**Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values**




$T_{amb}$ = 25 °C

(1) $I_C/I_B = 20$

(2) $I_C/I_B = 10$

(3) $I_C/I_B = 5$

**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**

# 8. Test information

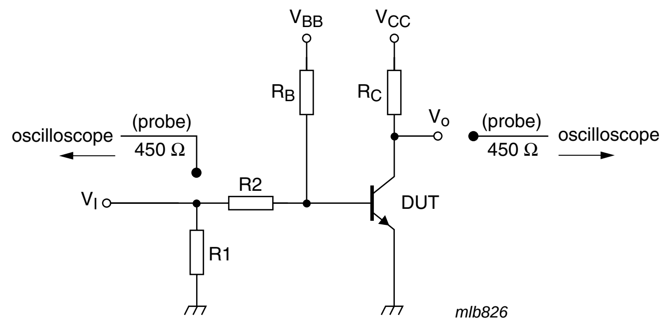



**Fig 12. Test circuit for switching times**

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline

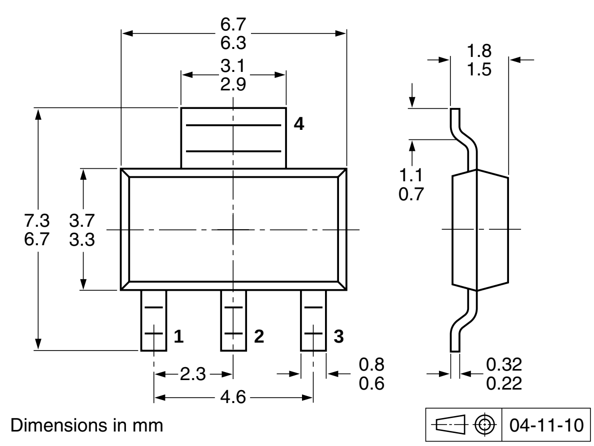



**Fig 13. Package outline SOT223 (SC-73)**

# 10. Packing information

**Table 8. Packing methods**

*The indicated -xxx are the last three digits of the 12NC ordering code.*[1]

| Type number | Package | Description | Packing quantity | |
|---|---|---|---|---|
| | | | **1000** | **4000** |
| PBHV8215Z | SOT223 | 8 mm pitch, 12 mm tape and reel | -115 | -135 |

[1] For further information and the availability of packing methods, see Section 14.

## 11. Soldering

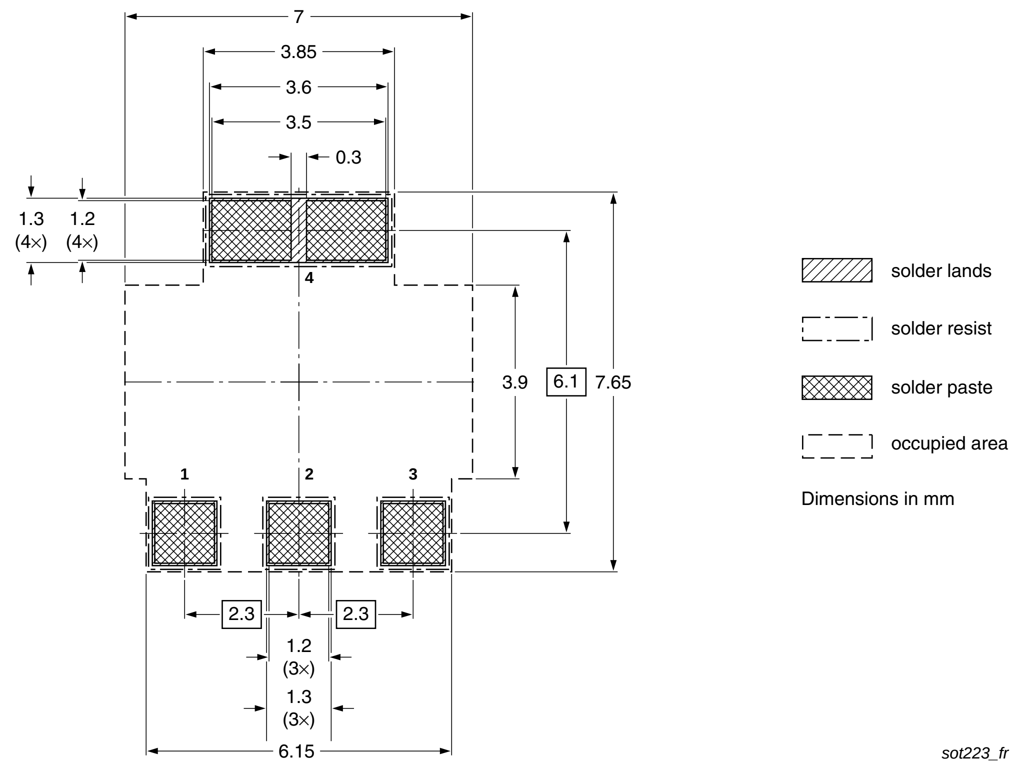



Fig 14. Reflow soldering footprint SOT223 (SC-73)

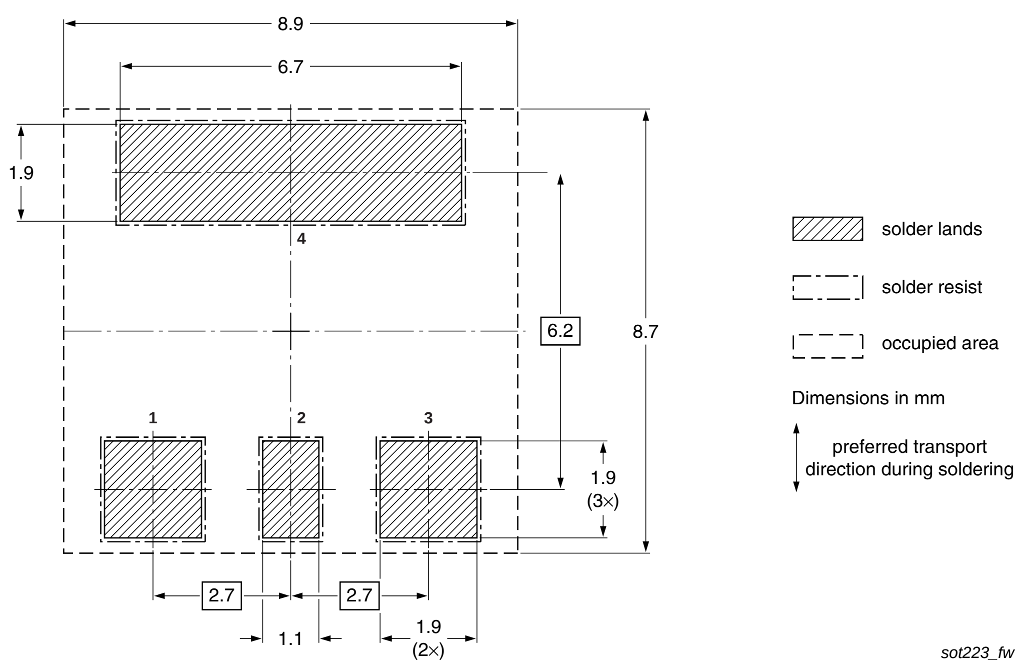



Fig 15. Wave soldering footprint SOT223 (SC-73)

## 12. Revision history

**Table 9. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| PBHV8215Z_1 | 20091111 | Product data sheet | - | - |

# 13. Legal information

## 13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 15. Contents





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**Date of release: 11 November 2009**

**Document identifier: PBHV8215Z_1**

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- Поставка образцов и прототипов;
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**Факс:** 8 (812) 320-02-42
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